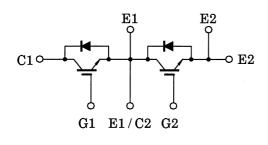
TOSHIBA GTR Module Silicon N Channel IGBT

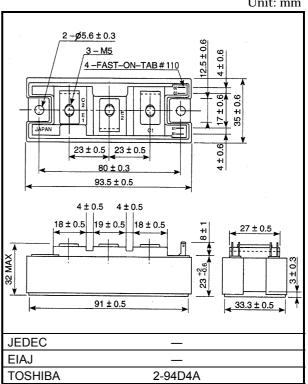
# **MG50Q2YS50**

**High Power Switching Applications** Motor Control Applications

- High input impedance •
- High speed :  $t_f = 0.3 \mu s$  (Max) @Inductive load
- Low saturation voltage •
- : VCE (sat) = 3.6V (Max)
- Enhancement-mode •
- Includes a complete half bridge in one package. .
- The electrodes are isolated from case.

### **Equivalent Circuit**





Weight: 202g

#### Maximum Ratings (Ta = 25°C)

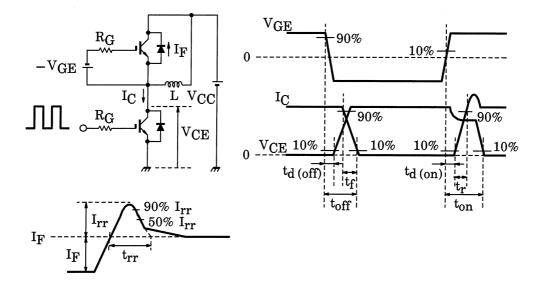
| Characteristic                             |     | Symbol                           | Rating                | Unit |  |
|--|-----|----------------------------------|-----------------------|------|--|
| Collector-emitter voltage                  |     | V <sub>CES</sub>                 | 1200                  | V    |  |
| Gate-emitter voltage                       |     | V <sub>GES</sub>                 | ±20                   | V    |  |
| Collector current                          | DC  | I <sub>C</sub><br>(25°C / 80°C)  | 78 / 50               | А    |  |
|  | 1ms | I <sub>CP</sub><br>(25°C / 80°C) | 156 / 100             | ~    |  |
| Forward current                            | DC  | ١ <sub>F</sub>                   | 50                    | А    |  |
|  | 1ms | I <sub>FM</sub>                  | 100                   | ~    |  |
| Collector power dissipation<br>(Tc = 25°C) |     | Pc                               | P <sub>C</sub> 400    |      |  |
| Junction temperature                       |     | Тј                               | 150                   | °C   |  |
| Storage temperature range                  |     | T <sub>stg</sub>                 | -40 ~ 125             | °C   |  |
| Isolation voltage                          |     | V <sub>Isol</sub>                | 2500<br>(AC 1 minute) | V    |  |
| Screw torque (Terminal / mounting)         |     | —                                | 3/3                   | N∙m  |  |

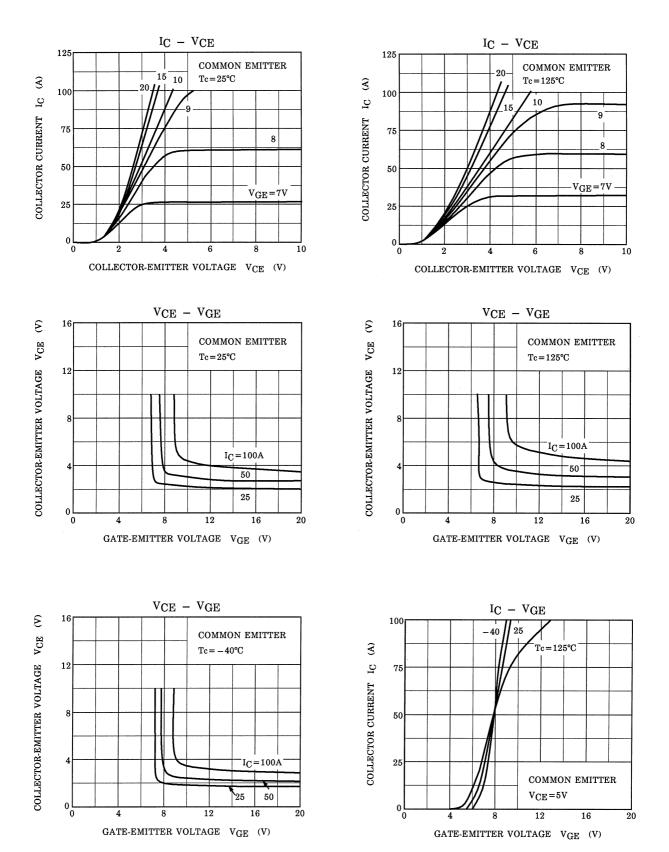
Unit: mm

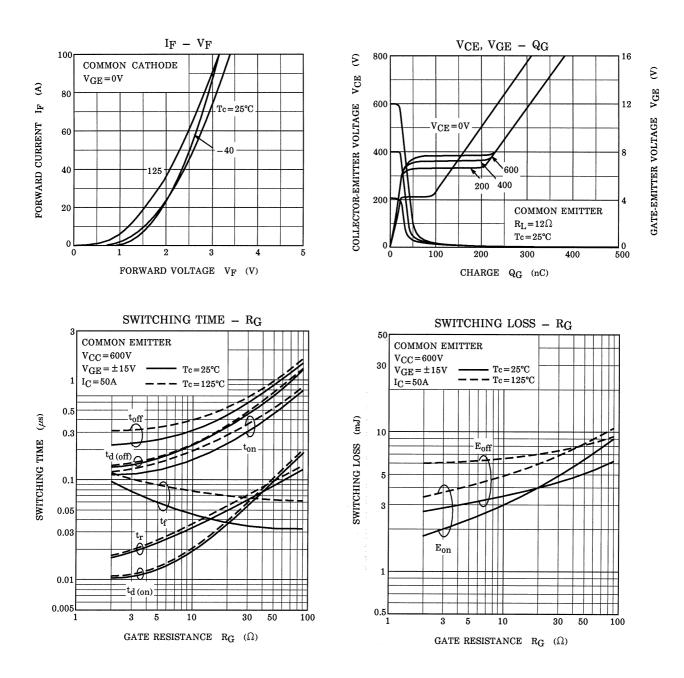
**Electrical Characteristics (Ta = 25°C)** 

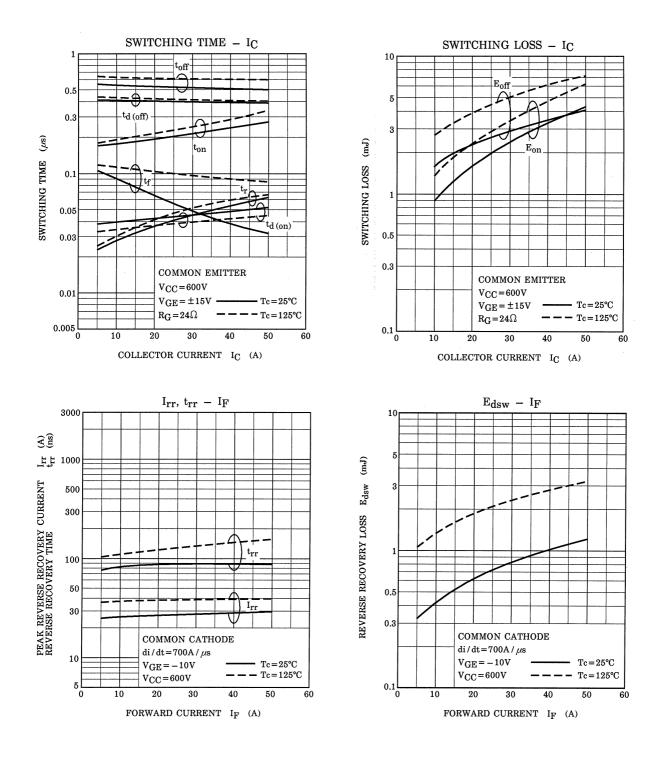
| Characteristic                       |                     | Symbol                | Test Condition   |  | Min | Тур. | Max  | Unit   |
|--------------------------------------|---------------------|-----------------------|--|--|-----|------|------|--------|
| Gate leakage current                 |                     | I <sub>GES</sub>      | V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0                                      |  |     | _    | ±500 | nA     |
| Collector cut-off current            |                     | ICES                  | V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0                                     |  | _   | _    | 1.0  | mA     |
| Gate-emitter cut-off voltage         |                     | V <sub>GE (OFF)</sub> | I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5V                                      |  | 3.0 | _    | 6.0  | V      |
| Collector-emitter saturation voltage |                     | V <sub>CE (sat)</sub> | I <sub>C</sub> = 50A,<br>V <sub>GE</sub> = 15V                                   | T <sub>j</sub> = 25°C                                | _   | 2.8  | 3.6  | v      |
|                                      |                     |                       |  | T <sub>j</sub> = 125°C                               | _   | 3.1  | 4.0  |        |
| Input capacitance                    |                     | Cies                  | V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0                                       | / <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz |     | 6.0  | _    | nF     |
| Switching time                       | Turn-on delay time  | t <sub>d (on)</sub>   |  |  | _   | 0.05 | _    |        |
|                                      | Rise time           | tr                    | Inductive load   |  | _   | 0.05 | _    | μs     |
|                                      | Turn-on time        | t <sub>on</sub>       | $V_{CC} = 600V$ $I_C = 50A$ $V_{GE} = \pm 15V$ $R_G = 24\Omega$                  |  | _   | 0.2  | _    |        |
|                                      | Turn-off delay time | t <sub>d (off)</sub>  |  |  | _   | 0.5  | _    |        |
|                                      | Fall time           | t <sub>f</sub>        |  | (Note 1)   | _   | 0.1  | 0.3  |        |
|                                      | Turn-off time       | t <sub>off</sub>      |  |  | _   | 0.6  | _    |        |
| Forward voltage                      |                     | VF                    | I <sub>F</sub> = 50 A, V <sub>GE</sub> = 0                                       |  | _   | 2.4  | 3.5  | V      |
| Reverse recovery time                |                     | t <sub>rr</sub>       | I <sub>F</sub> = 50 A, V <sub>GE</sub> = -10 V,<br>di / dt = 700 A / μs (Note 1) |  | _   | 0.1  | 0.25 | μs     |
| Thermal resistance                   |                     | R <sub>th (j-c)</sub> | Transistor stage<br>Diode stage  |  | _   | —    | 0.31 | °C / W |
|                                      |                     |                       |  |  | _   | _    | 0.94 |        |

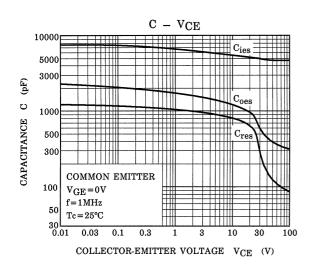
Note 1: Switching time and reverse recovery time test circuit & timing chart

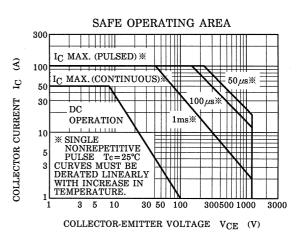


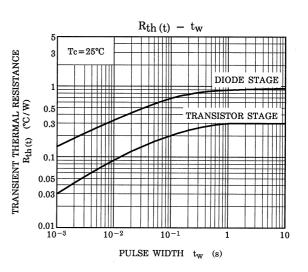


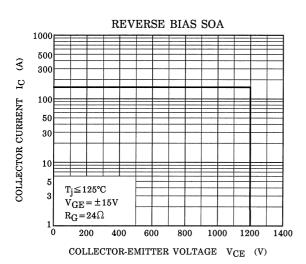


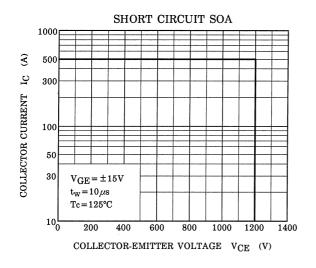












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